

ABSTRACT

A well structure in a high voltage device comprises a first well formed in a substrate, the first well having an opposite conductive type from the substrate; a second well isolated from the first well, the second well having the same conductive type as the substrate; a field stop implant region formed between the first well and the second well and spaced apart from each of the first well and the second well by a given distance, the field stop implant region having the same conductive type as the substrate; and a pick-up region overlapped on the field stop implant region, the pick-up region having the same conductive type as the field stop implant region.